

## **HIGH-POWER NPN SILICON POWER TRANSISTORS**

...designed for use in general-purpose amplifier and switching application.

## **FEATURES**

- \* Recommend for 100W High Fidelity Audio Frequency Amplifier Output stage
- \* complementary 2SB554

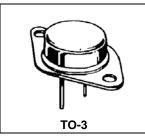
# NPN 2SD424

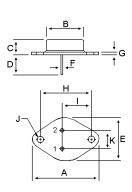
15 AMPERES POWER TRANSISTOR

180 VOLTS 150 WATTS

# **MAXIMUM RATINGS**

Rating	Symbol	2SD424	Unit
Collector-Emitter Voltage	$V_{CEO}$	180	V
Collector-Base Voltage	V <sub>CBO</sub>	180	V
Emitter-Base Voltage	$V_{EB}$	5.0	V
Collector Current-Continuous -Peak	I <sub>C</sub> I <sub>CM</sub>	15 18	Α
Base Current	I <sub>B</sub>	3.0	А
Total Device Dissipation @ T <sub>C</sub> =25°C Derate above 25°C	P <sub>D</sub>	150 1.2	W W/°C
Operating and Storage Junction Temperature Range	$T_{J}$ , $T_{STG}$	-55 to +150	°C



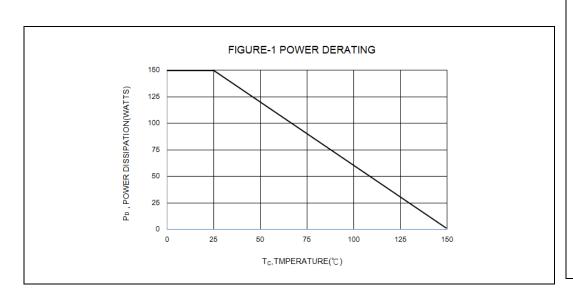




	LIMETERS	
MIN	MAX	
38.75	39.96	
19.28	22.23	
7.96	9.28	
11.18	12.19	
25.20	26.67	
0.92	1.09	
1.38	1.62	
29.90	30.40	
16.64	17.30	
3.88	4.36	
10.67	11.18	
	38.75 19.28 7.96 11.18 25.20 0.92 1.38 29.90 16.64 3.88	

# THERMAL CHARACTERISTICS

Characteristic	Symbol	Мах	Unit
Thermal Resistance Junction to Case	R <sub>θJC</sub>	0.83	°C/W



ELECTRICAL CHARATERISTICS (T<sub>c</sub>=25°C unless otherwise noted)

Characteristic	Symbol	Min.	Max	Unit
OFFCHARACTERISTICS				
Collector-Emitter Breakdown Voltage (I <sub>C</sub> = 50 mA, I <sub>B</sub> = 0)	V <sub>(BR)CEO</sub>	180		V
Collector-Cutoff Current ( V <sub>CB</sub> = 180 V, I <sub>E</sub> =0 )	І <sub>СВО</sub>		100	uA
Emitter Cutoff Current ( $V_{BE}$ = 5.0 V, $I_{c}$ = 0)	I <sub>EBO</sub>		100	uA
ON CHARACTERISTICS(1)				
DC current gain ( I <sub>C</sub> = 2.0 A, V <sub>CE</sub> = 5.0 V )	h <sub>FE</sub>	40	140	
Collector-Emitter Saturation Voltage ( I <sub>C</sub> = 10 A, I <sub>B</sub> = 1.0 A )	V <sub>CE(sat)</sub>		3.0	V
Base-Emitter On Voltage ( I <sub>C</sub> =10 A, V <sub>CE</sub> =5.0 V )	V <sub>BE(on)</sub>		2.5	V
DYNAMIC CHARATERISTICS				

\*hFE(2) Classification :

40 R 80	70 O 140
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<sup>(1)</sup> Pulse test: Pulse Width  $\leq$  300 s, Duty Cycle  $\leq$  2.0%



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